



STW14NM50

N-CHANNEL 500V - 0.32Ω - 14A TO-247

MDmesh™ Power MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW14NM50	500V	< 0.35Ω	14 A

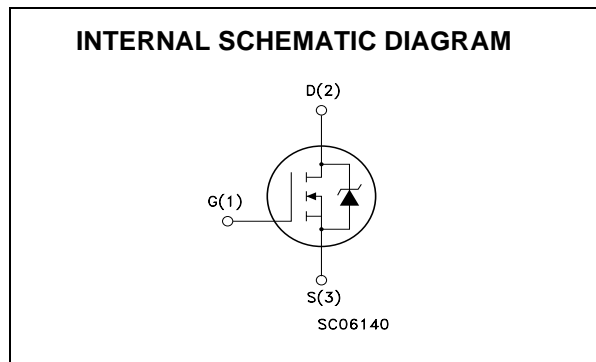
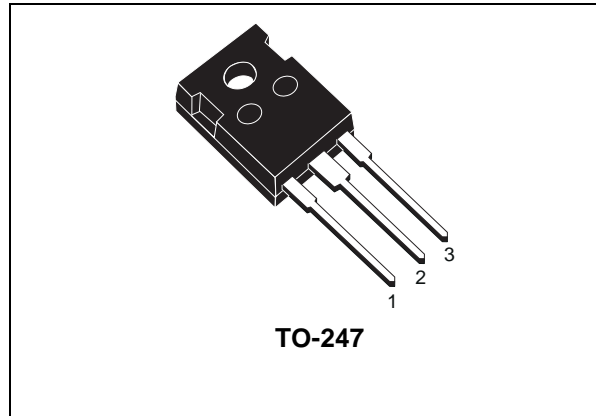
- TYPICAL R_{DS(on)} = 0.32Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS

DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's propriety strip technique yields overall dynamic performance that is significantly better than that of similar completion's products.

APPLICATIONS

The MDmesh™ family is very suitable for increase the power density of high voltage converters allowing system miniaturization and higher efficiencies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate- source Voltage	±30	V
I _D	Drain Current (continuous) at T _C = 25°C	14	A
I _D	Drain Current (continuous) at T _C = 100°C	8.8	A
I _{DM} ⁽¹⁾	Drain Current (pulsed)	56	A
P _{TOT}	Total Dissipation at T _C = 25°C	175	W
	Derating Factor	1.28	W/°C
dv/dt	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*)Pulse width limited by safe operating area
(*)Limited only by maximum temperature allowed

(1)I_{SD} ≤ 12A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

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THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.715	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	12	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	400	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 6A		0.3	0.35	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 6A		5.2		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1000		pF
C _{oss}	Output Capacitance			180		pF
C _{rss}	Reverse Transfer Capacitance			25		pF
C _{oss eq.} (1)	Equivalent Output Capacitance	V _{GS} = 0V, V _{DS} = 0V to 400V		90		pF
R _G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω

1. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250\text{ V}$, $I_D = 6\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		20		ns
t_r	Rise Time			10		ns
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$		28		nC
Q_{gs}	Gate-Source Charge			8		nC
Q_{gd}	Gate-Drain Charge			15		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400\text{ V}$, $I_D = 12\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		19		ns
t_f	Fall Time			8		ns
t_c	Cross-over Time			18		ns

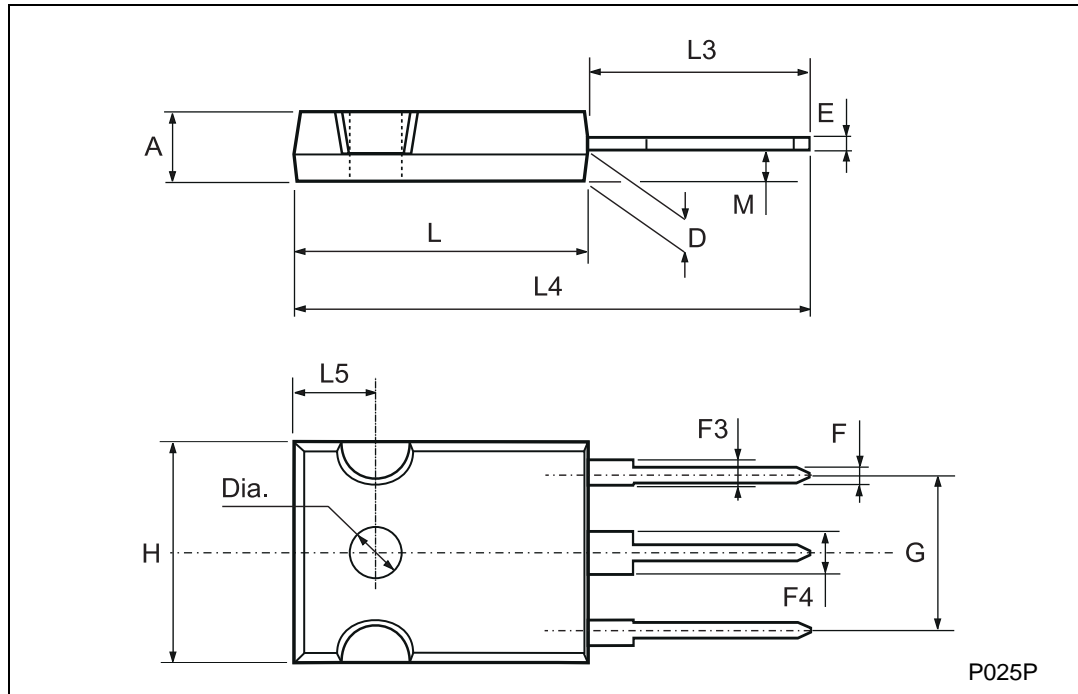
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				12	A
$I_{SDM}^{(1)}$	Source-drain Current (pulsed)				48	A
$V_{SD}^{(2)}$	Forward On Voltage	$I_{SD} = 12\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_j = 25^\circ\text{C}$ (see test circuit, Figure 5)		270		ns
Q_{rr}	Reverse Recovery Charge			2.23		μC
I_{RRM}	Reverse Recovery Current			16.5		A
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		340		ns
Q_{rr}	Reverse Recovery Charge			3		μC
I_{RRM}	Reverse Recovery Current			18		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



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